

PTO/SB/08b (02-09)  
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Substitute for form 1449/PTO  <h2 style="text-align: center; margin: 10px 0;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h2> <p style="text-align: center; margin: 5px 0;">(Use as many sheets as necessary)</p>		<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <th colspan="2" style="text-align: center; font-weight: normal;">Complete if Known</th> </tr> <tr> <td style="width: 50%;">Application Number</td> <td>10/581,950-Conf. #8737</td> </tr> <tr> <td>Filing Date</td> <td>August 18, 2008</td> </tr> <tr> <td>First Named Inventor</td> <td>Anderson</td> </tr> <tr> <td>Art Unit</td> <td><del>2622</del> 2894</td> </tr> <tr> <td>Examiner Name</td> <td>D. T. Nguyen</td> </tr> <tr> <td>Attorney Docket Number</td> <td>GWS-008</td> </tr> </table>		Complete if Known		Application Number	10/581,950-Conf. #8737	Filing Date	August 18, 2008	First Named Inventor	Anderson	Art Unit	<del>2622</del> 2894	Examiner Name	D. T. Nguyen	Attorney Docket Number	GWS-008
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A12*	US-5,945,730	08-31-1999	Sicard et al.	
	A13*	US-6,261,944	07-17-2001	Mehta et al.	
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	A19*	US-7,432,595	10-07-2008	Okada	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	B1	WO-2005-057617 A3	06-23-2005	Great Wall Semiconductor	

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>6</sup>
	C4	Darwish et al., "Scaling Issues in Lateral Power MOSFETs," Proc. 1998 Intl. Symp. On Power Semiconductor Devices & Ics, pp. 329-332.		
	C5	International Search Report and Written Opinion for PCT/US2004/040698, dated August 8, 2005.		
	C6	International Search Report and Written Opinion for PCT/US2004/40197, mailed November 21, 2008.		
	C7	Pavler et al., "Bi-directional FlipFET™ MOSFETS for Cell Phone Battery Protection Circuits," PCIM 2001.		
	C8	Shen et al., "Lateral Discrete Power MOSFET: Enabling Technology for Next-Generation, MHz-Frequency, High-Density DC/DC Converters," APEC (2004).		
	C9	Sun et al., "0.35μm, 43 μA/cm <sup>2</sup> 6mΩ Power MOSFET to Power Future Microprocessor," IEEE pp. 77-79 (1999).		
Examiner Signature	/Duy Nguyen/			Date Considered 06/02/2009

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LIBC/3561130